

Atty Docket No.: MART4591

Serial No.: 09/759,899

In The Abstract:

Please substitute the following clean copy text for the pending abstract:

31 --A method to treat a silicon oxide material generated during a removal of a photoresist layer configured above a silicon oxynitride surface is described in which the photo resist layer is first removed by an oxygen plasma treatment process, followed by an argon plasma treatment process to overetch the SiON layer and to remove the silicon oxide material.--

In The Claims

Please substitute the following clean copy text for the pending claims of the same number:

5. (currently amended) A method to remove a silicon oxide material formed during a removal of a photoresist layer configured above a silicon containing material, and the method in removing the silicon oxide material comprising:

B2 an oxygen plasma to remove a majority of the photoresist layer, wherein the silicon oxide material is resulted from a reaction between the silicon containing material and the oxygen plasma; and

an ion bombardment method using an inert gas plasma to remove a residual of the photoresist layer and to treat the silicon oxide material.